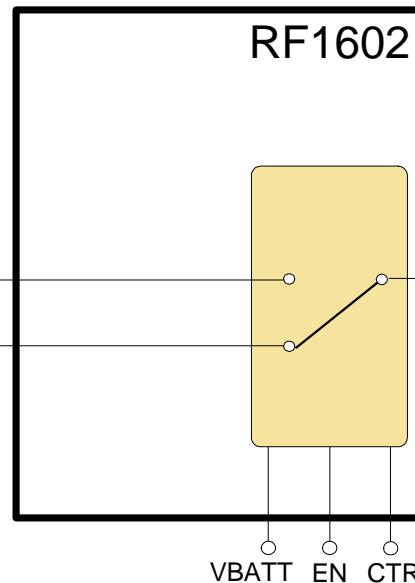




Package: QFN, 2mm x 2mm x 0.55mm



Functional Block Diagram

Features

- Low Frequency to 3.5GHz Operation
- Low Insertion Loss, Typ. 0.3dB at 1GHz
- Very High Isolation, Typ. 42dB at 1GHz
- High Linearity, IIP2 Typ. 129dBm
- Direct Connection to V_{BATT}
- Compatible with Low Voltage Logic (V_{HIGH} Minimum = 1.3V)
- No External DC Blocking Capacitors Required on RF Paths Unless DC is applied Externally
- 2kV HBM Rating on All Ports

Applications

- SV-LTE, WCDMA, GSM
- Post PA Switching
- General Purpose Switching Applications

Product Description

The RF1602 is a single-pole dual-throw (SPDT) switch designed for switching applications requiring very low insertion loss and high power handling capability coupled with minimal DC power consumption. The excellent linearity performance achieved by the RF1602 makes it ideal for use in SV-LTE, WCDMA, and CDMA applications. The RF1602 offers very high isolation between RF ports providing greater separation between transmit and receive paths. The RF1602 is packaged in a very compact 2mm x 2mm x 0.55mm 12-Pin QFN package.

Ordering Information

RF1602 Broadband SPDT Switch
RF1602PCBA-41X Fully Assembled Evaluation Board

Optimum Technology Matching® Applied

| | | | |
|--------------------------------------|--------------------------------------|---|-----------------------------------|
| <input type="checkbox"/> GaAs HBT | <input type="checkbox"/> SiGe BiCMOS | <input type="checkbox"/> GaAs pHEMT | <input type="checkbox"/> GaN HEMT |
| <input type="checkbox"/> GaAs MESFET | <input type="checkbox"/> Si BiCMOS | <input checked="" type="checkbox"/> Si CMOS | <input type="checkbox"/> RF MEMS |
| <input type="checkbox"/> InGaP HBT | <input type="checkbox"/> SiGe HBT | <input type="checkbox"/> Si BJT | <input type="checkbox"/> LDMOS |

RF MICRO DEVICES®, RFMD®, Optimum Technology Matching®, Enabling Wireless Connectivity™, PowerStar®, POLARIS™ TOTAL RADIO™ and UltimateBlue™ are trademarks of RFMD, LLC. BLUETOOTH is a trademark owned by Bluetooth SIG, Inc., U.S.A. and licensed for use by RFMD. All other trade names, trademarks and registered trademarks are the property of their respective owners. ©2012, RF Micro Devices, Inc.

Absolute Maximum Ratings

| Parameter | Rating | Unit |
|--|-------------|------|
| Maximum V _{BATT} | 6.0 | V |
| Maximum EN | 3.0 | V |
| Maximum CTRL | 3.0 | V |
| Maximum Power Handling (6:1 VSWR, Temp = 25 °C) | +36 | dBm |
| Operating Temperature | -30 to +85 | °C |
| Storage Temperature | -40 to +125 | °C |



Caution! ESD sensitive device.

Exceeding any one or a combination of the Absolute Maximum Rating conditions may cause permanent damage to the device. Extended application of Absolute Maximum Rating conditions to the device may reduce device reliability. Specified typical performance or functional operation of the device under Absolute Maximum Rating conditions is not implied.

The information in this publication is believed to be accurate and reliable. However, no responsibility is assumed by RF Micro Devices, Inc. ("RFMD") for its use, nor for any infringement of patents, or other rights of third parties, resulting from its use. No license is granted by implication or otherwise under any patent or patent rights of RFMD. RFMD reserves the right to change component circuitry, recommended application circuitry and specifications at any time without prior notice.



RFMD Green: RoHS compliant per EU Directive 2002/95/EC, halogen free per IEC 61249-2-21, < 1000ppm each of antimony trioxide in polymeric materials and red phosphorus as a flame retardant, and <2% antimony in solder.

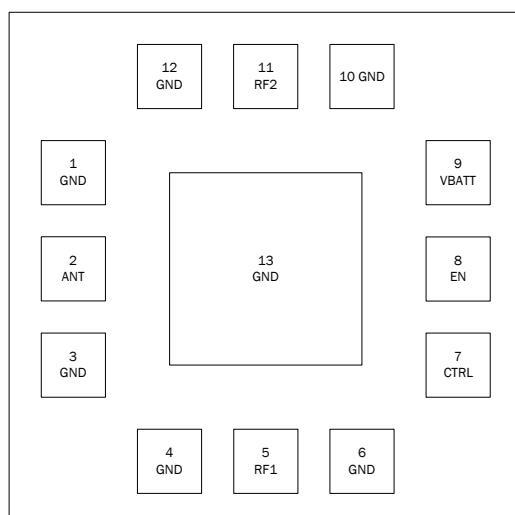
| Parameter | Specification | | | Unit | Condition | |
|------------------------|---------------|------|------|------|---|--|
| | Min. | Typ. | Max. | | | |
| | | | | | (All Nominal Test Conditions Unless Otherwise Stated) V _{BATT} = 3.5V, Temperature = 25 °C, All RF ports terminated in 50Ω | |
| Insertion Loss | | | | | | |
| RF1 to ANT, RF2 to ANT | | 0.30 | 0.40 | dB | 400MHz to 1GHz | |
| | | 0.30 | 0.45 | dB | 1.0GHz to 2.0GHz | |
| | | 0.35 | 0.50 | dB | 2.0GHz to 2.5GHz | |
| | | 0.40 | 0.55 | dB | 2.5GHz to 3.5GHz | |
| Isolation | | | | | | |
| RF1 to RF2, RF2 to RF1 | 37 | 42 | | dB | 400MHz to 1GHz | |
| | 31 | 34 | | dB | 1.0GHz to 2.0GHz | |
| | 30 | 32 | | dB | 2.0GHz to 2.5GHz | |
| | 25 | 29 | | dB | 2.5GHz to 3.5GHz | |
| RF Port Return Loss | | | | | | |
| ANT, RF1, RF2 | 10 | 15 | | dB | 400MHz to 3.5GHz | |
| 900MHz Harmonics | | | | | | |
| Second Harmonic | | -95 | -75 | dBc | P _{IN} = 35dBm | |
| Third Harmonic | | -90 | -75 | dBc | | |
| 1800MHz Harmonics | | | | | | |
| Second Harmonic | | -95 | -75 | dBc | P _{IN} =33dBm | |
| Third Harmonic | | -90 | -75 | dBc | | |
| IIP2 | | | | | | |
| RF1, RF2, ANT (Cell) | 122 | 129 | | dBm | Tone 1: 836.5MHz at +26dBm Tone 2: 1718MHz at -20dBm Receive Freq: 881.5MHz | |
| RF1, RF2, ANT (AWS) | 122 | 129 | | dBm | Tone 1: 1732.5MHz at +26dBm Tone 2: 3865MHz at -20dBm Receive Freq: 2132.5MHz | |
| RF1, RF2, ANT (PCS) | 122 | 129 | | dBm | Tone 1: 1880MHz at +26dBm Tone 2: 3840MHz at -20dBm Receive Freq: 1960MHz | |
| RF1, RF2, ANT (IMT) | 122 | 129 | | dBm | Tone 1: 1950MHz at +26dBm Tone 2: 4090MHz at -20dBm Receive Freq: 2140MHz | |

| Parameter | Specification | | | Unit | Condition |
|--|---------------|------|------|------|--|
| | Min. | Typ. | Max. | | |
| IIP3 SV-LTE | | | | | |
| RF1, RF2, ANT (Cell) | | 83 | | dBm | Tone 1: 786MHz at +23dBm Tone 2: 825MHz at +14dBm Receive Freq: 747MHz |
| RF1, RF2, ANT (Cell) | | 80 | | dBm | Tone 1: 782MHz at +23dBm Tone 2: 827MHz at +14dBm Receive Freq: 872MHz |
| IIP3 | | | | | |
| RF1, RF2, ANT (Cell) | 70 | 75 | | dBm | Tone 1: 836.5MHz at +26dBm Tone 2: 791.5MHz at -20dBm Receive Freq: 881.5MHz |
| RF1, RF2, ANT (IMT) | 70 | 75 | | dBm | Tone 1: 1950MHz at +26dBm Tone 2: 1760MHz at -20dBm Receive Freq: 2140MHz |
| Max Operating Power | | | | | |
| | | | 36 | dBm | 50Ω, Temp = 25°C |
| | | | 35 | dBm | VSWR = 6:1, Temp = -30° to +85°C |
| Supply and Control Signal Characteristics | | | | | |
| Supply Voltage, V_{BATT} | 2.7 | 3.5 | 4.6 | V | |
| Supply Current, V_{BATT} | | | | | |
| EN = HIGH | | 100 | 200 | µA | |
| EN = LOW | | 14 | 20 | µA | |
| Control Voltage (EN, CTRL) | | | | | |
| V_{HIGH} | 1.3 | 1.8 | 2.7 | V | |
| V_{LOW} | | 0 | 0.45 | V | |
| Control Current | | | | | |
| I_{HIGH} | | 2.5 | 5 | µA | |
| I_{LOW} | | 1 | 3 | µA | |
| Switching Time | | | | | |
| Switching Speed ON | | 2 | 5 | µs | All combination; 50% control to 90% RF ON |
| Switching Speed RF OFF | | 2 | 5 | µs | All combinations; 50% control to 10% RF OFF |
| Start Up Time from Shut-down | | | 5 | µs | Maximum set up time for the switch to reach fully compliant operation |

Pin Names and Description

| Pin | Function | Description |
|-----|---------------------|---|
| 1 | GND | Ground. |
| 2 | ANT | Single ended RF port. |
| 3 | GND | Ground. |
| 4 | GND | Ground. |
| 5 | RF1 | Single ended RF port. |
| 6 | GND | Ground. |
| 7 | CTRL | Switch logic control input. |
| 8 | EN | Switch logic control input, shutdown for low leakage current. |
| 9 | VBATT | Supply voltage from battery. |
| 10 | GND | Ground. |
| 11 | RF2 | Single ended RF port. |
| 12 | GND | Ground. |
| 13 | Package Base | Ground. |

Pin Out



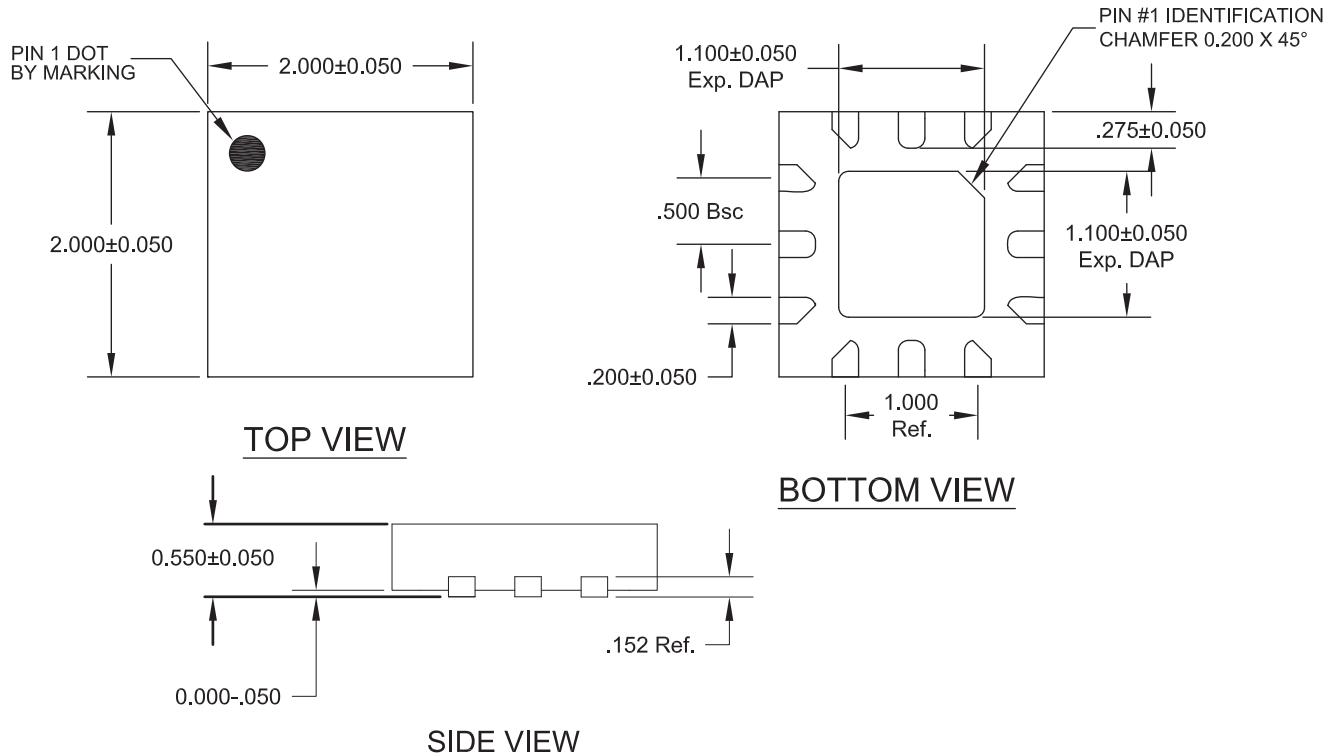
Top View

Control Logic

| State | V_{BATT} | CTRL | EN | RF Path |
|----------|--------------|------------|------------|----------|
| 1 | 2.7V to 4.6V | V_{HIGH} | V_{HIGH} | ANT-RF2 |
| 2 | 2.7V to 4.6V | V_{LOW} | V_{HIGH} | ANT-RF1 |
| Shutdown | 2.7V to 4.6V | Don't Care | V_{LOW} | Shutdown |

The switch is operable in 3 states. The switch is designed for two modes: active and shutdown. Assuming VBATT is always between 2.7V and 4.6V the switch is controlled by the EN voltage. When EN is HIGH the switch is active and when EN is LOW the switch is in standby mode.

Package Drawing



PCB Surface Finish

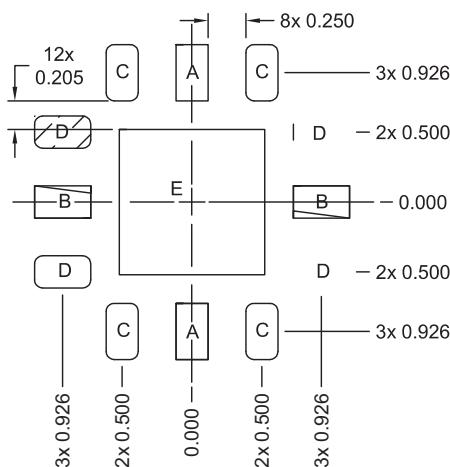
The PCB surface finish used for RFMD's qualification process is electroless nickel, immersion gold. Typical thickness is 3 μ inch to 8 μ inch gold over 180 μ inch nickel.

PCB Land Pattern Recommendation

PCB land patterns for RFMD components are based on IPC-7351 standards and RFMD empirical data. The pad pattern shown has been developed and tested for optimized assembly at RFMD. The PCB land pattern has been developed to accommodate lead and package tolerances. Since surface mount processes vary from company to company, careful process development is recommended.

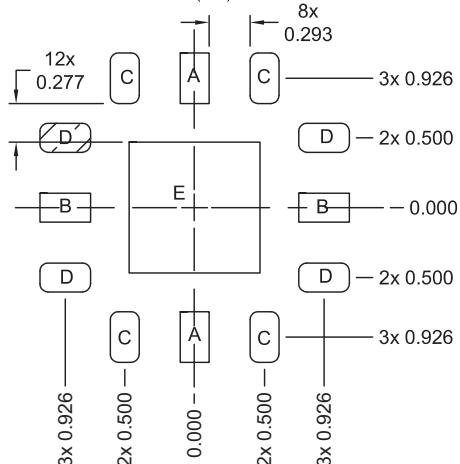
PCB Metal Land and Solder Mask Pattern

A = 0.230 x 0.402 (mm) Typ
B = 0.402 x 0.230 (mm) Typ
C = 0.230 x 0.402 (mm) Rounded Rectangle 0.058 Corner Radius
D = 0.402 x 0.230 (mm) Rounded Rectangle 0.058 Corner Radius
E = 1.040 x 1.040 (mm)



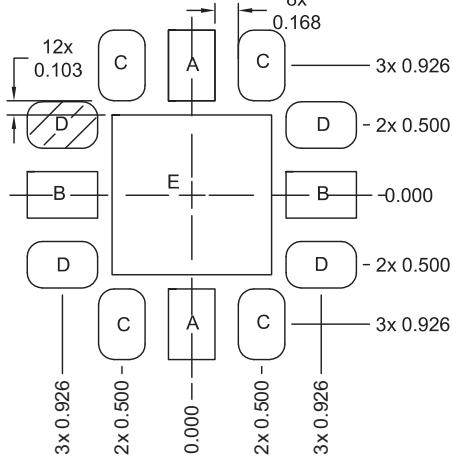
PCB METAL PATTERN

A = 0.207×0.362 (mm)
B = 0.362×0.207 (mm)
C = 0.207×0.362 (mm) Rounded Rectangle 0.052 Corner Radius
D = 0.362×0.207 (mm) Rounded Rectangle 0.052 Corner Radius
E = 0.936×0.936 (mm)



PCB STENCIL PATTERN

A = 0.332×0.504 (mm) Typ PCB
B = 0.504×0.332 (mm) Typ
C = 0.332×0.504 (mm) Rounded Rectangle 0.109 Corner Radius
D = 0.504×0.332 (mm) Rounded Rectangle 0.109 Corner Radius
E = 1.142×1.142 (mm) 8x



PCB SOLDER MASK PATTERN

Shaded area represents Pin 1 location.

Evaluation Board Schematic

